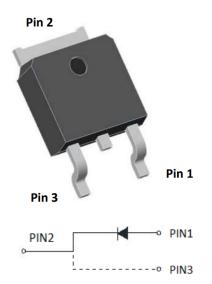






Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F (135°C)}	16A
Qc	54.1nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-252

Molding compound meets UL 94 V-0 flammability

rating, RoHS-compliant, halogen-free

• **Terminals**: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112010DG1
Reverse voltage (repetitive peak) @ T _i =25°C	V_{RRM}	٧	1200
Reverse voltage (Surge Peak) @ T _j =25°C	V_{RSM}	٧	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	٧	1200
Continuous forward current @ T _c =25°C			33
Continuous forward current @ T _c =135°C	I _F	Α	16
Continuous forward current @ T _c =157°C			10
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	105
Power Dissipation@ T _c =25°C	-	w	211
Power Dissipation@ T₀=110°C	Р _{тот}	VV	91
i²t Value@ Tc=25°C ,tp=10ms	∫i²dt	A ² S	55
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175





■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drap	V _F	V	I _F =10A, T _j =25°C	1.47	1.65
Forward voltage drop	VF	V	I _F =10A, T _j =175°C	2.25	2.7
Poverse leakage current			V _R =1200V, T _j =25°C	1	15
Reverse leakage current	I _R	l _R μA	V _R =1200V, T _j =175°C	20	-
Total capacitive charge	Q _C	nC	V_R =800V, T_j =25°C , QC = $\int_0^{VR}C(V)dV$	54.1	
			V _R =0V, f=1MHZ	768.3	-
Total capacitance	С	pF	V _R =400V, f=1MHZ	51.7	-
			V _R =800V, f=1MHZ	37.2	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	13.8	-

PARAMETER	SYMBOL	UNIT	Per device
Thermal resistance	$R_{ heta J-C}$	°C W	0.71

■Characteristics (Typical)

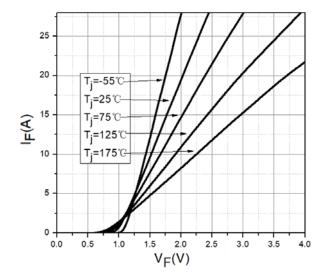


Figure 1. Forward Characteristics

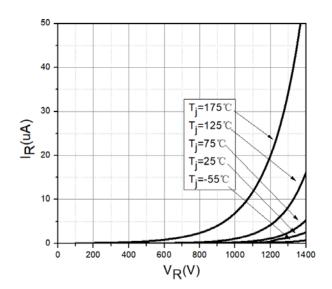


Figure 2. Reverse Characteristic

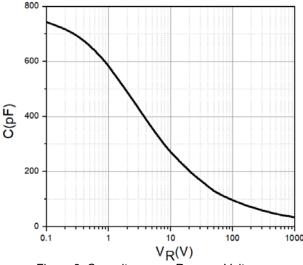


Figure 3. Capacitance vs. Reverse Voltage

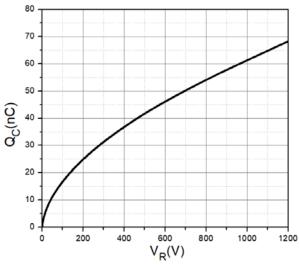


Figure 4. Total Capacitance Charge vs. Reverse Voltage

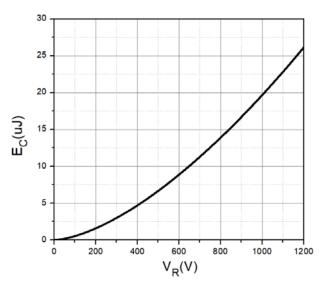


Figure 5. Capacitance Stored Energy

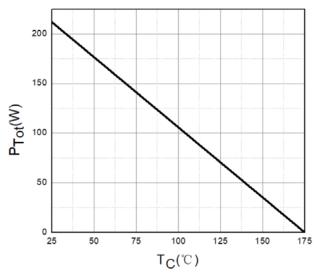


Figure 6. Power Derating

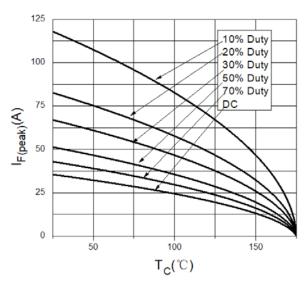


Figure 7. Current Derating

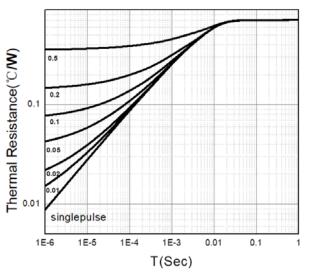


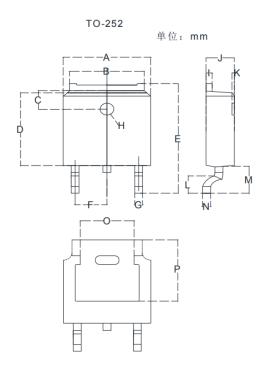
Figure 8. Transient Thermal Impedance







■Outline Dimensions



TO-252			
Dim	Min	Max	
Α	6.500	6.700	
В	5.100	5.460	
С	1.400	1.800	
D	6.000	6.200	
E	10.000	10.400	
F	2.166	2.366	
G	0.660	0.860	
Н	Ф1.050	Ф1.350	
- 1	0.460	0.580	
J	2.200	2.400	
K	0	0.300	
L	0.890	2.290	
М	2.730	3.080	
N	0.430	0.580	
0	4.20	4.95	
Р	5.15	5.45	



YJD112010DG1



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